

CIR-S4DUSN2104G

DDR4 DIMM 2133MHz 4GB

Description

CIR-S4DUSN2104G is a CMOS Double Data Rate IV (DDR4) Synchronous DRAM module, in Fine Ball Grid Array (FBGA) packages on a 288pin glass-epoxy substrate.

DDR4 unbuffered UDIMM series offers fully synchronous operations referenced to both rising and falling edges of the clock. The data paths are internally pipelined and 8-bit prefetched to achieve very high bandwidth.

Specifications

Density	4GB
Pin Count	288pin
Type	Unbuffered
Dimensions	133.35mm x 31.25mm
ECC	Non-ECC
Component Config	512M x 8 bit
Data Rate	2133 Mbps
CAS Latency	15
Voltage:	1.2V
PCB Layers	8
Operating Temp.(TCASE)	0°C~+85°C
Module Ranks	Single Rank

Features

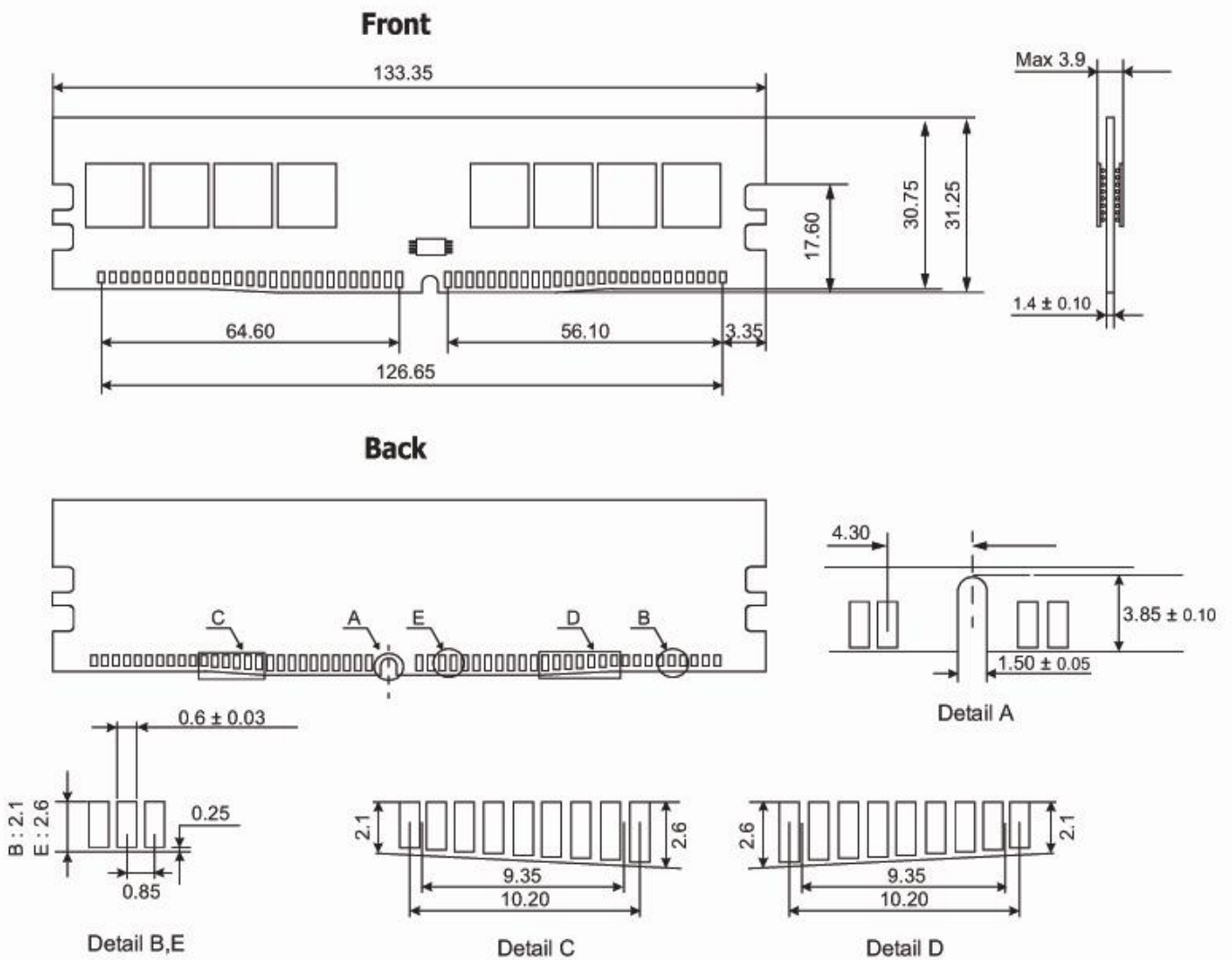
- JEDEC standard
- VDD=VDDQ = 1.2V±0.06V (1.14V~1.26V)
- Programmable CAS Latency(posted CAS): 11,12,13,14,15
- 8-bit pre-fetch
- 16 Banks (4 Bank Groups)
- Internal(self) calibration : Internal self calibration through ZQ pin
- On Die Termination using ODT pin
- Average Refresh Period
 - 7.8us (TCASE ≤ 85°C)
 - 3.9us (85°C < TCASE < 95°C)
- DRAM operating temperature range
 - Commercial (0°C ≤ TCASE ≤ 85°C)
 - Industrial (-40°C ≤ TCASE ≤ 85°C)
- Asynchronous Reset pin supported
- Burst Length: 8 or BC4
- POD (Pseudo Open Drain) interface for data input/output
- Serial presence detect (SPD)
- All of products are Halogen-free
- All of Lead-Free products are compliant for RoHS

Speed Grade

Frequency Grade	Data Transfer Rate	CAS Latency Support					CL-tRCD-tRP
		CL11	CL12	CL13	CL14	CL15	
DDR4-2133	PC4-17000	1600	1600	1866	1866	2133	15-15-15

Package Dimensions

Unit: mm



Tolerances : ± 0.15mm unless otherwise specified